TOSHIBA CMOS Digital Integrated Circuit   Silicon Monolithic

TC74HC7292AP,TC74HC7292AF

Programmable Divider/Timer

The TC74HC7292A is a high speed CMOS PROGRAMMABLE DIVIDER/TIMER fabricated with silicon gate C^2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The TC74HC7292A can divide from 2^2 to 2^{31}.

CK1 and CK2 are clock inputs, either one may be used for clock gating.

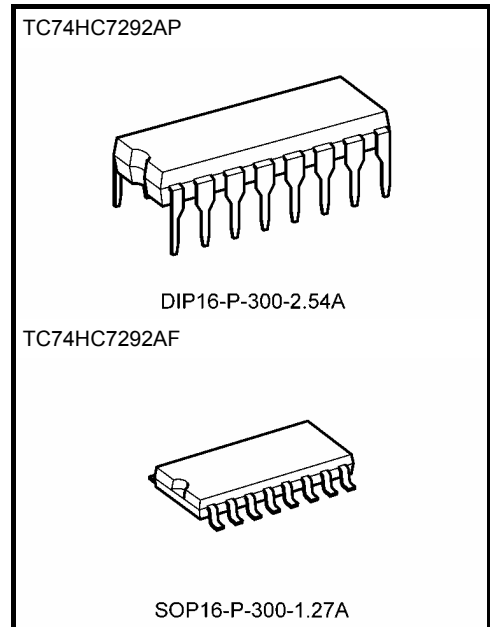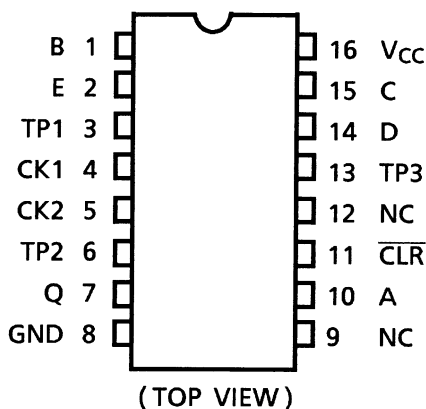It features an active-low clear input to initialize the state of all flip-flops.

To facilitate incoming inspection, test points are provided. (TP1, TP2 and TP3)

All inputs are equipped with protection circuits against static discharge or transient excess voltage.
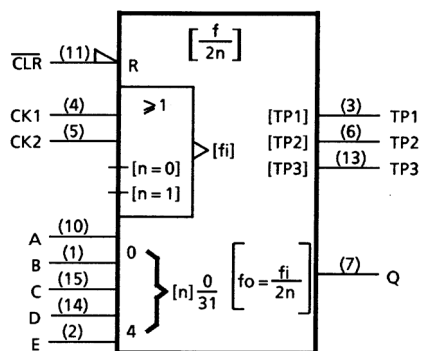
Features

- High speed: f_{max} = 70 MHz (typ.) at V_{CC} = 5 V
- Low power dissipation: I_{CC} = 4 μA (max) at Ta = 25°C
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Output drive capability: 10 LSTTL loads
- Symmetrical output impedance: $|I_{OH}|$ = I_{OL} = 4 mA (min)
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2 to 6 V
- Pin and function compatible with 74LS292

TC74HC7292AP

DIP16-P-300-2.54A

TC74HC7292AF

SOP16-P-300-1.27A

Weight
DIP16-P-300-2.54A   : 1.00 g (typ.)
SOP16-P-300-1.27A   : 0.18 g (typ.)

Pin Assignment

B	1	16	V_{CC}
E	2	15	C
TP1	3	14	D
CK1	4	13	TP3
CK2	5	12	NC
TP2	6	11	$\overline{CLR}$
Q	7	10	A
GND	8	9	NC

(TOP VIEW)

IEC Logic Symbol

Truth Table

$\overline{CLR}$	CK1	CK2	Q Output Mode
L	X	X	Cleared to L
H	⤒	L	Up Count
H	L	⤒	
H	H	X	No Change
H	X	H	

Programming Inputs					Frequency Division							
					Q		TP1		TP2		TP3	
E	D	C	B	A	Binary	Decimal	Binary	Decimal	Binary	Decimal	Binary	Decimal
L	L	L	L	L	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit
L	L	L	L	H	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit	Inhibit
L	L	L	H	L	2^2	4	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	L	L	H	H	2^3	8	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	L	H	L	L	2^4	16	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	L	H	L	H	2^5	32	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	L	H	H	L	2^6	64	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	L	H	H	H	2^7	128	2^9	512	2^{17}	131,072	2^{24}	16,777,216
L	H	L	L	L	2^8	256	2^9	512	2^{17}	131,072	2^2	4
L	H	L	L	H	2^9	512	2^9	512	2^{17}	131,072	2^2	4
L	H	L	H	L	2^{10}	1,024	2^9	512	2^{17}	131,072	2^4	16
L	H	L	H	H	2^{11}	2,048	2^9	512	2^{17}	131,072	2^4	16
L	H	H	L	L	2^{12}	4,096	2^9	512	2^{17}	131,072	2^6	64
L	H	H	L	H	2^{13}	8,192	2^9	512	2^{17}	131,072	2^6	64
L	H	H	H	L	2^{14}	16,384	2^9	512	Disabled Low		2^8	256
L	H	H	H	H	2^{15}	32,768	2^9	512	Disabled Low		2^8	256
H	L	L	L	L	2^{16}	65,536	2^9	512	2^3	8	2^{10}	1,024
H	L	L	L	H	2^{17}	131,072	2^9	512	2^3	8	2^{10}	1,024
H	L	L	H	L	2^{18}	262,144	2^9	512	2^5	32	2^{12}	4,096
H	L	L	H	H	2^{19}	524,288	2^9	512	2^5	32	2^{12}	4,096
H	L	H	L	L	2^{20}	1,048,576	2^9	512	2^7	128	2^{14}	16,384
H	L	H	L	H	2^{21}	2,097,152	2^9	512	2^7	128	2^{14}	16,384
H	L	H	H	L	2^{22}	4,194,304	Disabled Low		2^9	512	2^{16}	65,536
H	L	H	H	H	2^{23}	8,388,608	Disabled Low		2^9	512	2^{16}	65,536
H	H	L	L	L	2^{24}	16,777,216	2^3	8	2^{11}	2,048	2^{18}	262,144
H	H	L	L	H	2^{25}	33,554,432	2^3	8	2^{11}	2,048	2^{18}	262,144
H	H	L	H	L	2^{26}	67,108,864	2^5	32	2^{13}	8,192	2^{20}	1,048,576
H	H	L	H	H	2^{27}	134,217,728	2^5	32	2^{13}	8,192	2^{20}	1,048,576
H	H	H	L	L	2^{28}	268,435,456	2^7	128	2^{15}	32,768	2^{22}	4,194,304
H	H	H	L	H	2^{29}	536,870,912	2^7	128	2^{15}	32,768	2^{22}	4,194,304
H	H	H	H	L	2^{30}	1,073,741,824	2^9	512	2^{17}	131,072	2^{24}	16,777,216
H	H	H	H	H	2^{31}	2,147,483,648	2^9	512	2^{17}	131,072	2^{24}	16,777,216

System Diagram
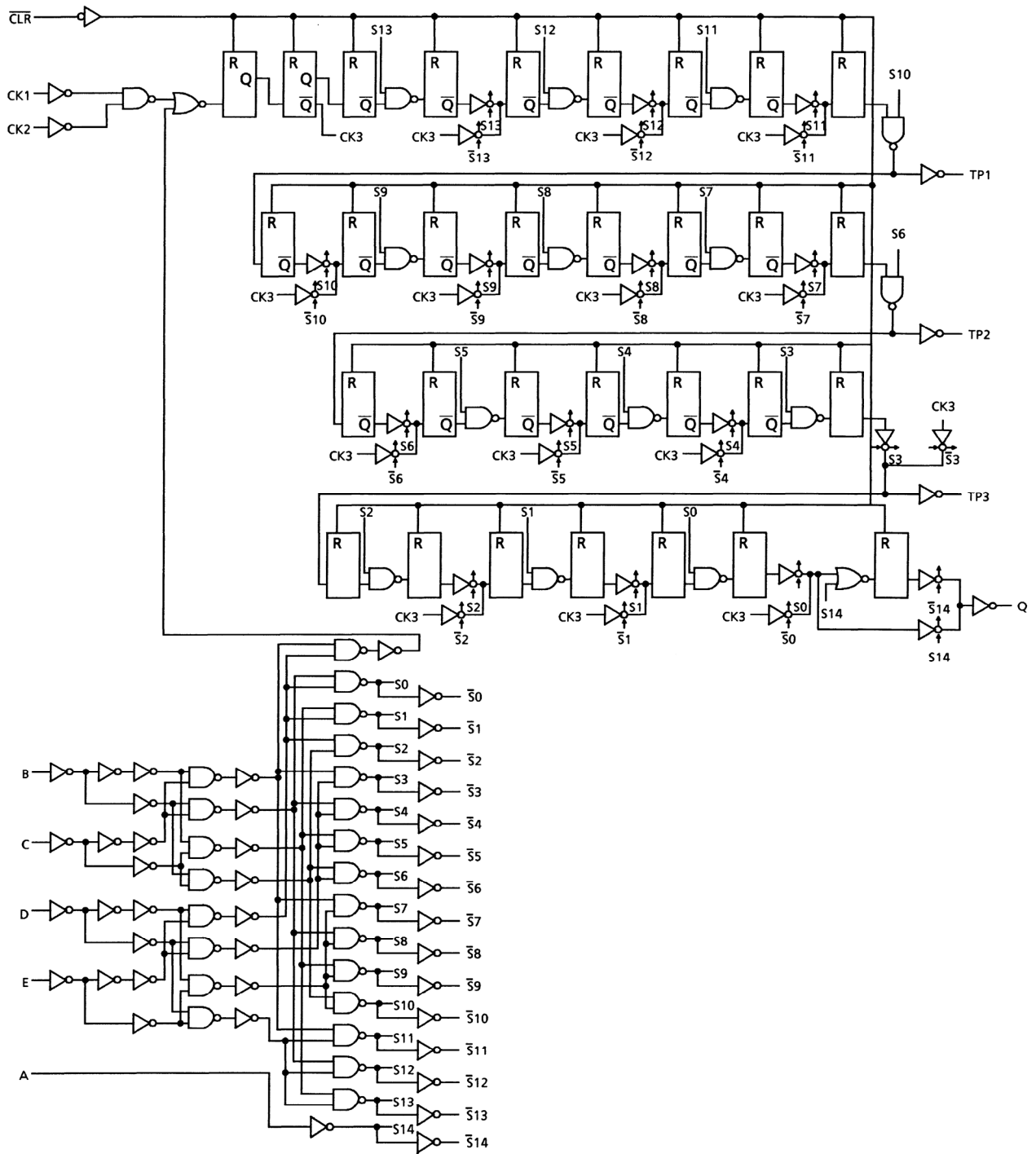
Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5 to 7	V
DC input voltage	V_{IN}	−0.5 to V_{CC} + 0.5	V
DC output voltage	V_{OUT}	−0.5 to V_{CC} + 0.5	V
Input diode current	I_{IK}	±20	mA
Output diode current	I_{OK}	±20	mA
DC output current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±50	mA
Power dissipation	P_D	500 (DIP) (Note 2)/180 (SOP)	mW
Storage temperature	T_{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = −40 to 65°C. From Ta = 65 to 85°C a derating factor of −10 mW/°C shall be applied until 300 mW.

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2 to 6	V
Input voltage	V_{IN}	0 to V_{CC}	V
Output voltage	V_{OUT}	0 to V_{CC}	V
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	t_r, t_f	0 to 1000 (V_{CC} = 2.0 V) 0 to 500 (V_{CC} = 4.5 V) 0 to 400 (V_{CC} = 6.0 V)	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		V_{CC} (V)	Ta = 25°C			Ta = −40 to 85°C		Unit
					Min	Typ.	Max	Min	Max	
High-level input voltage	V_{IH}	—		2.0	1.50	—	—	1.50	—	V
				4.5	3.15	—	—	3.15	—	
				6.0	4.20	—	—	4.20	—	
Low-level input voltage	V_{IL}	—		2.0	—	—	0.50	—	0.50	V
				4.5	—	—	1.35	—	1.35	
				6.0	—	—	1.80	—	1.80	
High-level output voltage (Q)	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −20 μA	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0	—	5.9	—	
			I_{OH} = −4 mA	4.5	4.18	4.31	—	4.13	—	
			I_{OH} = −5.2 mA	6.0	5.68	5.80	—	5.63	—	
Low-level output voltage (Q)	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20 μA	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
			I_{OL} = 4 mA	4.5	—	0.17	0.26	—	0.33	
			I_{OL} = 5.2 mA	6.0	—	0.18	0.26	—	0.33	
Input leakage current	I_{IN}	V_{IN} = V_{CC} or GND		6.0	—	—	±0.1	—	±1.0	μA
Quiescent supply current	I_{CC}	V_{IN} = V_{CC} or GND		6.0	—	—	4.0	—	40.0	μA

Timing Requirements (input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Ta = 25°C		Ta = −40 to 85°C	Unit
				Typ.	Limit	Limit	
Minimum pulse width (CK)	$t_{W (L)}$ $t_{W (H)}$	—	2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum pulse width ($\overline{CLR}$)	$t_{W (L)}$	—	2.0	—	175	220	ns
			4.5	—	35	44	
			6.0	—	30	37	
Minimum removal time	t_{rem}	—	2.0	—	5	5	ns
			4.5	—	5	5	
			6.0	—	5	5	
Clock frequency	f	—	2.0	—	5	4	MHz
			4.5	—	27	22	
			6.0	—	32	26	

AC Characteristics (C_L = 15 pF, V_{CC} = 5 V, Ta = 25°C, input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Output transition time (Q)	t_{TLH} t_{THL}	—	—	4	8	ns
Output transition time (TP)	t_{TLH} t_{THL}	—	—	25	44	ns
Propagation delay time (CK-Q)	t_{pLH} t_{pHL}	—	—	42	75	ns
Propagation delay time ($\overline{CLR}$ -Q)	t_{pHL}	—	—	36	62	ns
Maximum clock frequency	f_{max}	—	30	70	—	MHz

AC Characteristics (C_L = 50 pF, input: t_r = t_f = 6 ns)

Characteristics	Symbol	Test Condition	V_{CC} (V)	Ta = 25°C Min	Ta = 25°C Typ.	Ta = 25°C Max	Ta = −40 to 85°C Min	Ta = −40 to 85°C Max	Unit
Output transition time (Q)	t_{TLH} t_{THL}	—	2.0	—	27	75	—	95	ns
			4.5	—	9	15	—	19	
			6.0	—	8	13	—	16	
Output transition time (TP)	t_{TLH} t_{THL}	—	2.0	—	90	250	—	315	ns
			4.5	—	30	50	—	63	
			6.0	—	25	43	—	54	
Propagation delay time (CK-Q)	t_{pLH} t_{pHL}	—	2.0	—	150	425	—	530	ns
			4.5	—	48	85	—	106	
			6.0	—	41	72	—	90	
Propagation delay time ($\overline{CLR}$ -Q)	t_{pHL}	—	2.0	—	130	350	—	440	ns
			4.5	—	42	70	—	88	
			6.0	—	36	60	—	75	
Maximum clock frequency	f_{max}	—	2.0	5	20	—	4	—	MHz
			4.5	27	64	—	22	—	
			6.0	32	75	—	26	—	
Input capacitance	C_{IN}	—		—	5	10	—	10	pF
Power dissipation capacitance	C_{PD}	(Note)		—	22	—	—	—	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC} (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

Package Dimensions

DIP16-P-300-2.54A

Unit : mm
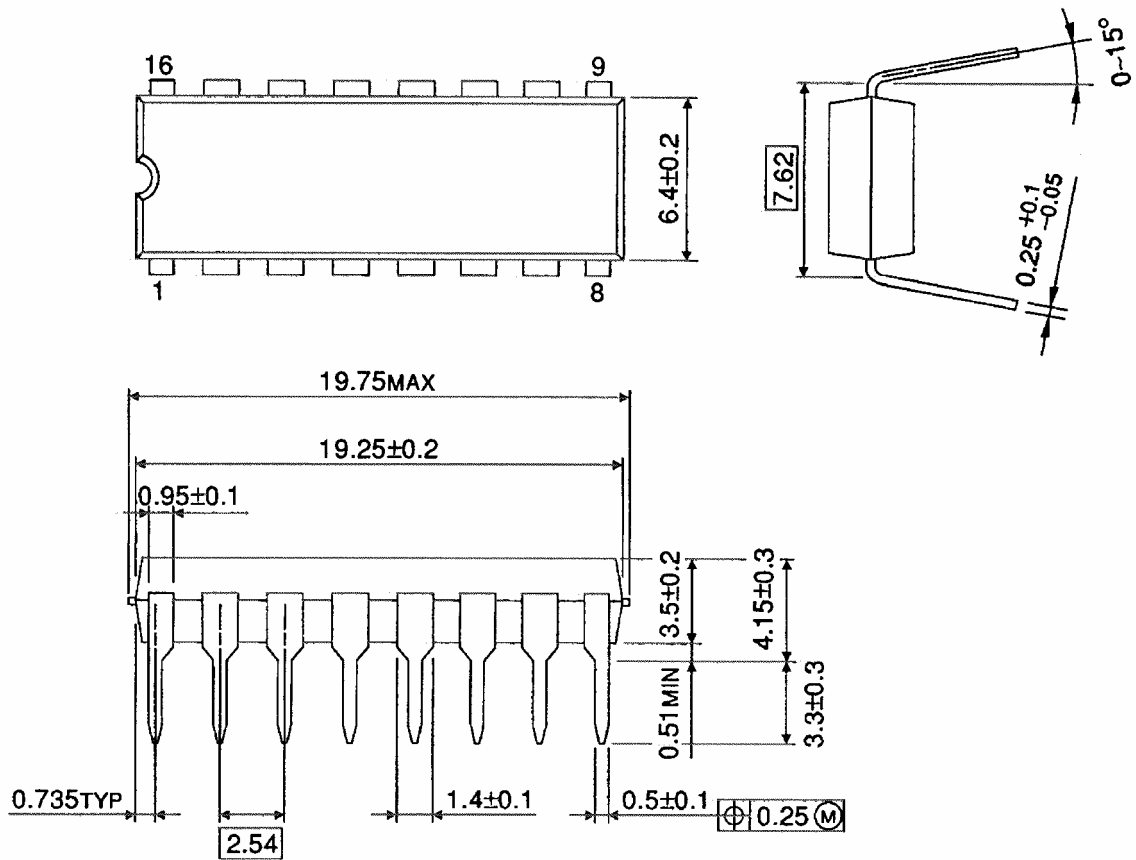
Weight: 1.00 g (typ.)

Package Dimensions

SOP16-P-300-1.27A   Unit: mm
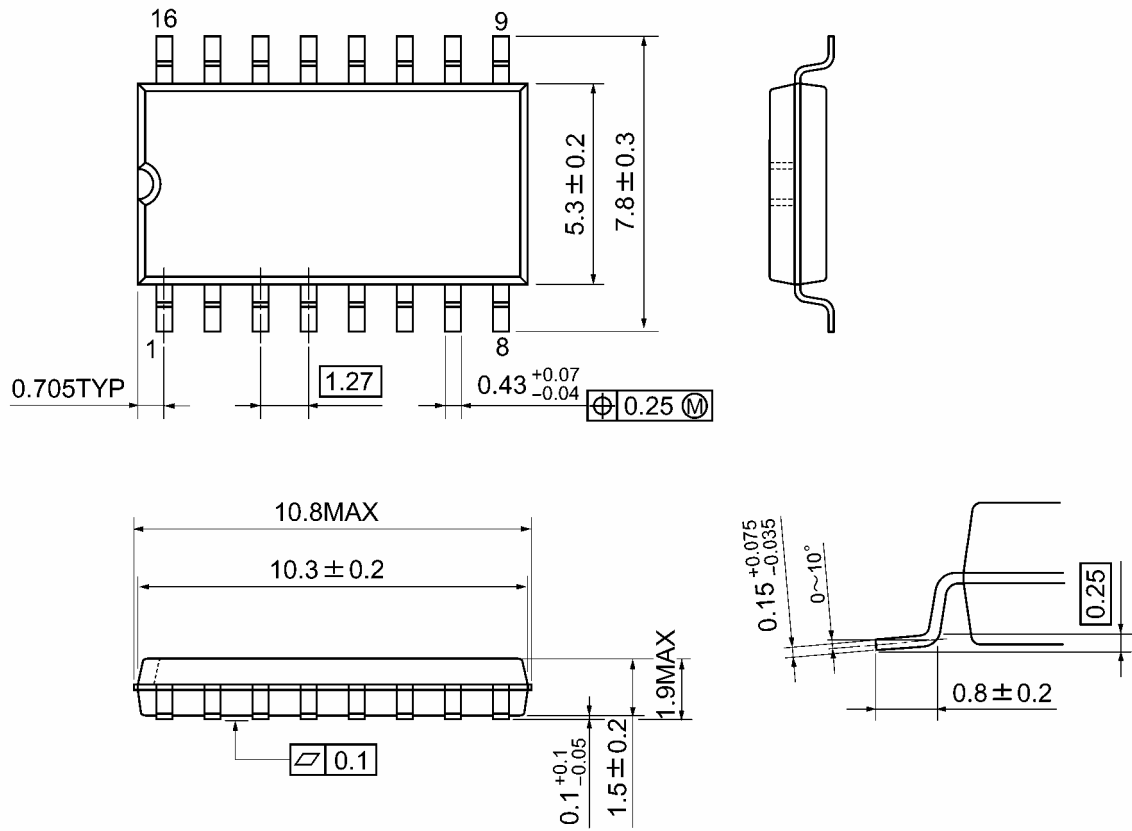
Weight: 0.18 g (typ.)

RESTRICTIONS ON PRODUCT USE